

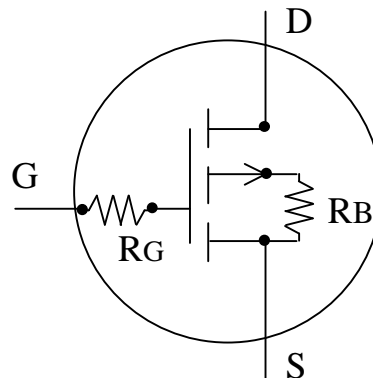
**2SJ652****ON Semiconductor®****SPICE PARAMETER****Pch MOS FET****model : BSIM3V3.2**

Parameter	Value	Parameter	Value	Parameter	Value
LEVEL	8				
VERSION	3.2	TNOM	27	TOX	6.0E-08
VTH0	-2.0	K1	3.12	K2	-0.04
NLX	1.7E-07	DVT0	1.12	DVT1	0.38
DVT2	-0.01	U0	230	UA	8.0E-10
UB	1.0E-21	VSAT	1.6E+05	A0	0.36
AGS	-0.3	A1	0	A2	1
RDSW	4.4E+06	PRWG	-3.7E-03	WR	1.22
WINT	0	LINT	-1.2E-07	VOFF	-2.7E-02
NFACTOR	0.87	CIT	0	CDSC	2.4E-04
CDSCD	0	ETA0	0	DSUB	0.96
PCLM	1.7	PDIBLC1	1.0E-03	PDIBLC2	2.0E-03
DROUT	0.96	PSCBE1	3.9E+09	PSCBE2	1.0E-05
PVAG	0.01	DELTA	1.0E-03	NGATE	1.0E+19
MOBMOD	1	NQSMOD	0	NOIMOD	1
CAPMOD	3	XPART	0.5	CGSO	6.0E-11
CGDO	2.0E-11	CGBO	0	CGSL	0
CGDL	4.0E-10	CKAPPA	1.2	CF	0
CLC	3.0E-09	CLE	0.8	DWC	0
DLC	-1.5E-07	NOFF	3.66	VOFFCV	-0.4
ACDE	1.0	MOIN	15	CJ	2.6E-04
MJ	0.45	PB	1.1	JS	3.5E-07
NJ	1.0	XTI	3.0	IJTH	0
KT1	-0.8	UTE	-0.5	PRT	9.0E+06
AT	3.3E+04				

Temp = 27 deg  
 L = 1.0E-6 m  
 W = 6169770E-6 m  
 AD = 6169770E-12 m2  
 RG = 3 ohm  
 RB = 0.01 ohm

Date : 2007/3/14

\*Information herein is for example only ;  
 It is not guaranteed for volume production.



ON Semiconductor